

Description

The SI2301CDS-T1-GE3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate chargeand operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.



General Features

 $V_{DS} = -20V, I_{D} = -2.3A$

 $R_{DS(ON)} < 140 \text{m} \Omega @ V_{GS} = -4.5 \text{V}$

 $R_{DS(ON)}$ < 170m Ω @ V_{GS} =-2.5V

G O

Application

PWM applications

Load switch

P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SI2301CDS-T1-GE3	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	-20	V
V _G s	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous	-2.3	А
Ідм	Drain Current-Pulsed (Note 1)	-9	А
P _D	Maximum Power Dissipation	0.65	W
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	178	°C/W

Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-20		-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V,V _{GS} =0V	-	-	-1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)	On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-0.4	-0.7	-1	V	
Drain-Source On-State Resistance		V _{GS} =-4.5V, I _D =-2A		130	140	mΩ	
Dialii-Source Off-State Resistance	R _{DS(ON)}	V_{GS} =-2.5V, I_{D} =-1.8A		152	170	mΩ	
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-2A	4	-	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	V _{DS} =-10V,V _{GS} =0V, F=1.0MHz	-	285	-	PF	
Output Capacitance	Coss		-	58	-	PF	
Reverse Transfer Capacitance	C _{rss}	r-1.0ivinz	-	32	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	9.8	-	nS	
Turn-on Rise Time	t _r	V_{DD} =-10V, R_L =5 Ω	-	4.9	-	nS	
Turn-Off Delay Time	t _{d(off)}	$V_{\text{GS}}\text{=-}4.5V, R_{\text{GEN}}\text{=}3\Omega$	-	20.5	_	nS	
Turn-Off Fall Time	t _f		-	7	-	nS	
Total Gate Charge	Qg	\/ - 40\/ - 24	-	2.9	-	nC	
Gate-Source Charge	Q _{gs}	V_{DS} =-10V, I_{D} =-2A, V_{GS} =-4.5V	-	0.45	-	nC	
Gate-Drain Charge	Q _{gd}	V _{GS} 4.5V	-	0.75	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-2A	-	-	-1.2	V	
Diode Forward Current (Note 2)	Is		-	-	-2.0	Α	

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

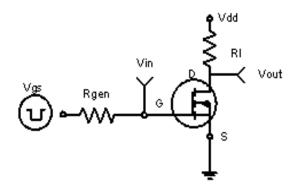


Figure 1:Switching Test Circuit

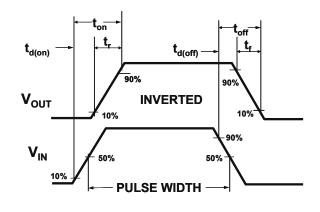


Figure 2:Switching Waveforms

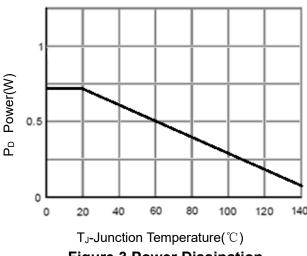


Figure 3 Power Dissipation

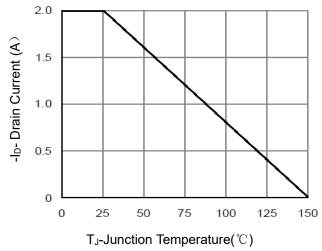


Figure 4 Drain Current

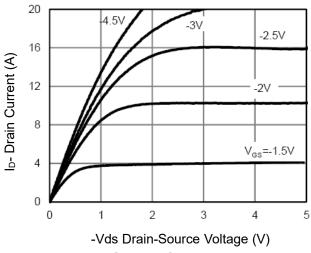


Figure 5 Output Characteristics

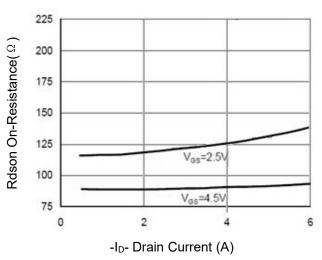


Figure 6 Drain-Source On-Resistance

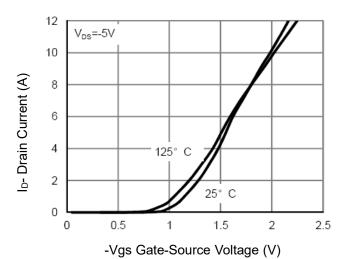


Figure 7 Transfer Characteristics

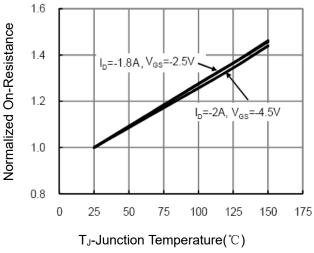


Figure 8 Drain-Source On-Resistance

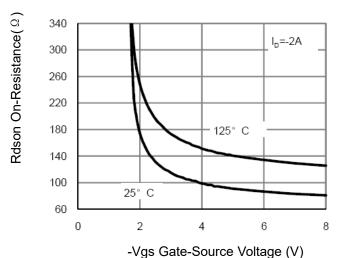


Figure 9 Rdson vs Vgs

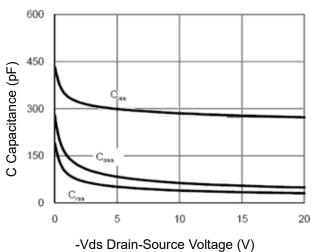


Figure 10 Capacitance vs Vds

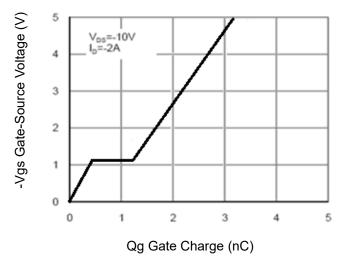


Figure 11 Gate Charge

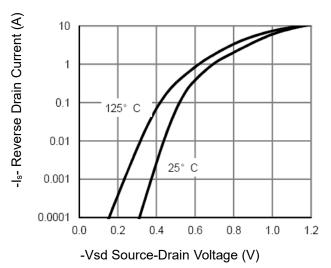


Figure 12 Source- Drain Diode Forward

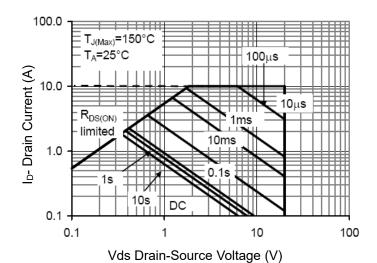


Figure 13 Safe Operation Area

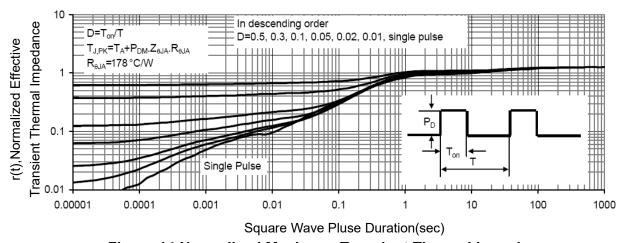
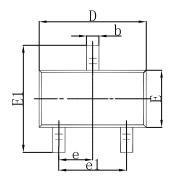
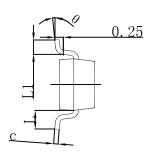
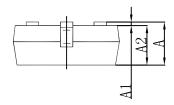


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Outline Dimensions

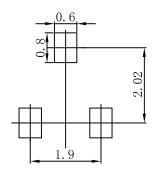






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	0 TYP 0.037 TYP		TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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